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*Zhi Chen; Kangguo Cheng; Jinju Lee; Lyding, J.W.; Hess, K.; Chetlur, S.*  
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*Wai-Kim Chim; Peng-Soon Lim*  
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*Bravaix, A.; Goguenheim, D.; Revil, N.; Vincent, E.*  
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*Ito, A.*

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*Joshi, A.B.; Kwong, D.L.*  
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